

Features:

- TO-78 hermetically sealed package
- High current transfer ratio
- 1 kV electrical isolation
- Base contact provided for conventional transistor biasing
- JAN, JANTX and JANTXV devices processed to MIL-PRF-19500
- Patent No. 4124860



Description:

Each isolator in this series consists of an infrared emitting diode and a NPN silicon phototransistor, which are mounted in a hermetically sealed TO-78 package. Devices are designed for military and/or harsh environments. The suffix letter "A" denotes the collector is electrically isolated from the case.

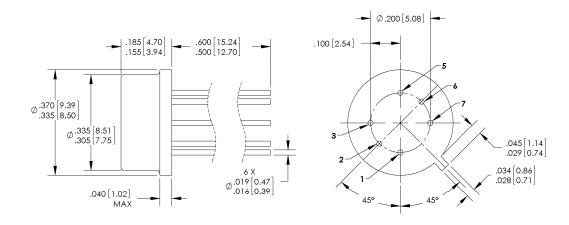
The JAN / JANTX / JANTXV 4N47, 4N47A, 4N48, 4N48A, 4N49, and 4N49A devices are processed to MIL-PRF-19500/548.

This series of 4N products are JEDEC registered, DSCC qualified.

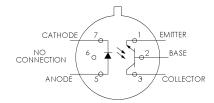
Please contact your local representative or OPTEK for more information.

Applications:

- · High-voltage isolation between input and output
- · Electrical isolation in dirty environments
- · Industrial equipment
- · Medical equipment
- Office



DIMENSIONS ARE IN INCHES [MIM]



Pin#	Function	Pin#	Function
3	Collector	5	Anode
2	Base	6	Open
1	Emitter	7	Cathode

BOTTOM VIEW

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Absolute Maximum Ratings (T _A =	= 25° C unless	otherwise noted)
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Storage Temperature Range	-55° C to +150° C
Operating Temperature Range	-55° C to +125° C
Input-to-Output Isolation Voltage	± 1.00 kVDC ⁽¹⁾
Lead Soldering Temperature [1/16 inch (1.6 mm) from case for 5 seconds with soldering iron]	260° C ⁽²⁾

Input Diode

Forward DC Current (65° C or below)	40 mA
Reverse Voltage	2 V
Power Dissipation	60 mW ⁽³⁾

Output Phototransistor:

Continuous Collector Current	50 mA
Collector-Emitter Voltage	40 V
Collector-Base Voltage	45 V
Emitter-Base Voltage	7.0 V
Power Dissipation	300 mW ⁽⁴⁾

Notes:

- 1. Measured with input leads shorted together and output leads shorted together.
- 2. RMA flux is recommended. Duration can be extended to 10 seconds maximum when flow soldering.
- 3. Derate linearly 1.0 mW/° C above 65° C.
- 4. Derate linearly 3.0 mW/° C above 25° C.

Ordering Information							
Part Number	Isolation Voltage (kV)	., (,		Processing MIL-PRF- 195000			
JAN4N47 or JAN4N47A							
JANTX4N47 or JANTX4N47A							
JANTXV4N47 or JANTXV4N47A			40	548			
JAN4N48 or JAN4N48A							
JANTX4N48 or JANTX4N48A	1	1 / 40					
JANTXV4N48 or JANTXV4N4A8							
JAN4N49 or JAN4N49A							
JANTX4N49 or JANTX4N49A							
JANTXV4N49 or JANTXV4N49A							

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Collector-Emitter Dark Current

Collector-Base Dark Current



 $V_{CE} = 20 \text{ V}, I_{B} = 0, I_{F} = 0, T_{A} = 100^{\circ} \text{ C}^{(1)}$

 $V_{CB} = 20 \text{ V}, I_{E} = 0, I_{F} = 0$

Electrical Characteristics (T_A = 25°C unless otherwise noted)

SYMBOL	PARAMETER	MIN	TYP	MAX	UNITS	TEST CONDITIONS
Input Diode						
V _F	Forward Voltage	0.80 1.00 0.70	- - -	1.50 1.70 1.30	V	$I_F = 10.0 \text{ mA}$ $I_F = 10.0 \text{ mA}, T_A = -55^{\circ} \text{ C}^{(1)}$ $I_F = 10.0 \text{ mA}, T_A = -100^{\circ} \text{ C}^{(1)}$
I _R	Reverse Current	-	-	100	μA	V _R = 2.0 V
Output Pl	hototransistor					
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	40	-	1	V	I _C = 1.0 mA, I _B = 0, I _F = 0
$V_{(BR)CBO} \\$	Collector-Base Breakdown Voltage	45	-	-	V	$I_C = 100 \mu A, I_B = 0, I_F = 0$
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	7	-	ı	V	I _E = 100 μA, I _C = 0, I _F = 0
I _{C(OFF)} ¹	Collector-Emitter Dark Current	-	-	100	nA	$V_{CE} = 20 \text{ V}, I_{B} = 0, I_{F} = 0$

100

10

μΑ

nΑ

I_{CB(OFF)}

I_{C(OFF)}²

Coupled						
	On-State Collector Current					1 - 10 mA V - 5 0 V 1 - 0
	JAN / JANTX / JANTXV 4N47 [A]	0.50 0.70 0.50	- - -	- - -		$\begin{split} I_F &= 1.0 \text{ mA, } V_{CE} = 5.0 \text{ V, } I_B = 0 \\ I_F &= 2.0 \text{ mA, } V_{CE} = 5.0 \text{ V, } I_B = 0, T_A = -55^{\circ} \text{ C}^{(1)} \\ I_F &= 2.0 \text{ mA, } V_{CE} = 5.0 \text{ V, } I_B = 0, T_A = 100^{\circ} \text{ C}^{(1)} \end{split}$
I _{C(ON)}	JAN / JANTX / JANTXV 4N48 [A]	1.00 1.40 1.00	- - -	5 - -	mA	$I_F = 1.0$ mA, $V_{CE} = 5.0$ V, $I_B = 0$ $I_F = 2.0$ mA, $V_{CE} = 5.0$ V, $I_B = 0$, $T_A = -55^{\circ}$ C ⁽¹⁾ $I_F = 2.0$ mA, $V_{CE} = 5.0$ V, $I_B = 0$, $T_A = 100^{\circ}$ C ⁽¹⁾
	JAN / JANTX / JANTXV 4N49 [A]	2.00 2.80 2.00	- - -	10 - -		$I_F = 1.0 \text{ mA}, V_{CE} = 5.0 \text{ V}, I_B = 0$ $I_F = 2.0 \text{ mA}, V_{CE} = 5.0 \text{ V}, I_B = 0, T_A = -55^{\circ} \text{ C}^{(1)}$ $I_F = 2.0 \text{ mA}, V_{CE} = 5.0 \text{ V}, I_B = 0, T_A = 100^{\circ} \text{ C}^{(1)}$
I _{CB(ON)}	On-State Collector Base	30	-	-	μΑ	V _{CB} = 5 V, I _E = 0, I _F = 10 mA
V _{CE(SAT)}	Collector-Emitter Saturation Voltage JAN / JANTX / JANTXV 4N47 [A] JAN / JANTX / JANTXV 4N48 [A] JAN / JANTX / JANTXV 4N49 [A]	- - -	- - -	0.30 0.30 0.30	V	$I_F = 2.0 \text{ mA}, I_C = 0.5 \text{ mA}, I_B = 0$ $I_F = 2.0 \text{ mA}, I_C = 1.0 \text{ mA}, I_B = 0$ $I_F = 2.0 \text{ mA}, I_C = 2.0 \text{ mA}, I_B = 0$
H _{FE}	DC Current Gain	100	-	-	V	V_{CE} = 5.0 V , I_{C} = 10.0 mA, I_{F} = 0 mA
R _{IO}	Resistance (Input-to-Output)	10 ¹¹	-	-	Ω	V _{I-O} = ± 1000 VDC ⁽³⁾
C _{IO}	Capacitance (Input-to-Output)	-	-	5	pF	V _{I-O} = 0 V, f = 1.0 MHz ⁽³⁾
T_R,T_F	Rise and Fall Time	-	-	20	μs	V_{CC} = 10.0 V , I_F = 5.0 mA, R_L = 100 Ω

Notes

- 1. Guaranteed but not tested.
- 2. Sample tested, LTPD = 10.
- 3. Measured with input leads shorted together and output leads shorted together.

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Typical Performance Curves

